

Voltage Detector (Reset) IC Series for Automotive Application

High Voltage Dual Output ADJ Type Window Voltage Detector (Reset) IC

BD48HW0G-C

General Description

ROHM's window voltage detector ICs are highly accurate, with low current consumption feature that uses CMOS process. It has dual N-channel open drain output. Detection voltage can be control by external resistors.

Features

- Nano Energy™
- AEC-Q100 Qualified^(Note 1)
- Functional Safety Supportive Automotive Products
- Under and Over Voltage Monitor
- Free Detection Voltage Setting by External Resistors
- Nch Open Drain Output
- Very Small, Lightweight and Thin Package
- SSOP6 Package is Similar to SOT-23-6 (JEDEC)

^(Note 1) Grade 1

Key Specifications

- | | |
|----------------------------------|---------------|
| ■ Over Voltage Detection: | 1.277 V (Typ) |
| ■ Under Voltage Detection: | 1.277 V (Typ) |
| ■ Ultra-Low Current Consumption: | 500 nA (Typ) |

Special Characteristics

- | | |
|-------------------------------|---------|
| ■ Detection Voltage Accuracy: | ±0.75 % |
|-------------------------------|---------|

Package

SSOP6:

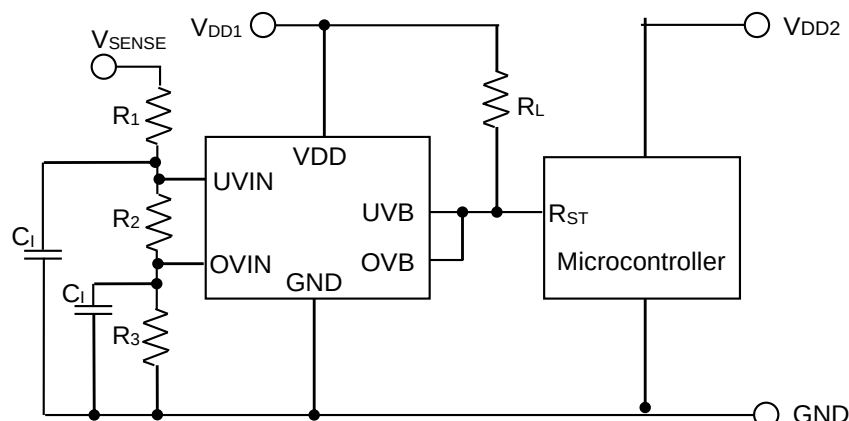
W (Typ) x D (Typ) x H (Max)
 2.9 mm x 2.8 mm x 1.25 mm



Application

All Automotive Devices That Requires Voltage Detection

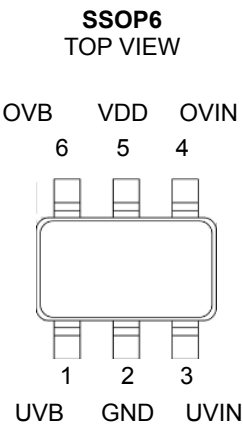
Typical Application Circuit



Nano Energy™ is a trademark or a registered trademark of ROHM Co., Ltd.

○Product structure : Silicon integrated circuit ○This product has no designed protection against radioactive rays.

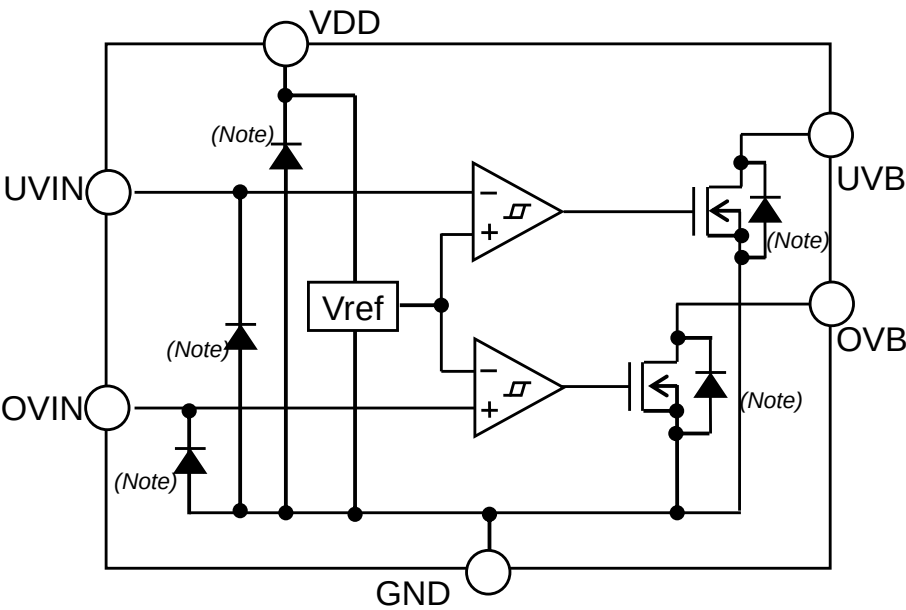
Pin Configuration



Pin Description

Pin No.	Pin Name	Function
1	UVB	Under voltage detection output pin
2	GND	GND
3	UVIN	Under voltage input
4	OVIN	Over voltage input
5	VDD	Power supply voltage
6	OVB	Over voltage detection output pin

Block Diagram



(Note) Parasitic Diode

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Limit	Unit
Power Supply Voltage	V _{DD}	-0.3 to +42	V
UVIN Pin Voltage	V _{UVIN}	-0.3 to +7	
OVIN Pin Voltage	V _{OVIN}	-0.3 to +7	
UVB Pin Voltage	V _{UVB}	(GND - 0.3) to +42	
OVB Pin Voltage	V _{OVB}	(GND - 0.3) to +42	
UVB Pin Output Current	I _{OUVB}	40	mA
OVB Pin Output Current	I _{OVB}	40	
Maximum Junction Temperature	T _{jmax}	+125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Thermal Resistance (Note 1)

Parameter	Symbol	Thermal Resistance (Typ)		Unit
		1s ^(Note 3)	2s2p ^(Note 4)	
SSOP6				
Junction to Ambient	θ _{JA}	376.5	185.4	°C/W
Junction to Top Characterization Parameter ^(Note 2)	Ψ _{JT}	40	30	°C/W

(Note 1) Based on JESD51-2A (Still-Air).

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 3) Using a PCB board based on JESD51-3.

(Note 4) Using a PCB board based on JESD51-7.

Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3 mm x 76.2 mm x 1.57 mmt

Top	
Copper Pattern	Thickness
Footprints and Traces	70 μm

Layer Number of Measurement Board	Material	Board Size
4 Layers	FR-4	114.3 mm x 76.2 mm x 1.6 mmt

Top		2 Internal Layers		Bottom	
Copper Pattern	Thickness	Copper Pattern	Thickness	Copper Pattern	Thickness
Footprints and Traces	70 μm	74.2 mm x 74.2 mm	35 μm	74.2 mm x 74.2 mm	70 μm

Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Operating Supply Voltage	V _{DD}	1.8	12.0	40.0	V
UVIN Pin Voltage	V _{UVIN}	0	-	6.0	V
OVIN Pin Voltage	V _{OVIN}	0	-	6.0	V
Operating Temperature	T _{opr}	-40	+25	+125	°C
Pull Up Resistance	R _L	10	100	1,000	kΩ

Function Explanation

1. Nano Energy™
Nano Energy™ is a combination of technologies which realizes ultra low quiescent current operation.

Electrical Characteristics (Unless otherwise specified Ta = -40 °C to +125 °C, V_{DD} = 1.8 V to 40 V)

Parameter	Symbol	Condition	Limit			Unit
			Min	Typ	Max	
Under Voltage Detection Voltage	V _{UVDET}	V _{UVIN} = H→L	1.2674	1.277	1.2866	V
Over Voltage Detection Voltage	V _{OVDDET}	V _{OVIN} = L→H	1.2674	1.277	1.2866	V
Hysteresis Voltage	V _{HYS}	-	-	1.0	-	%
Circuit Current	I _{DD}	-	-	500	2,000	nA
UVIN input current	I _{UVIN}	V _{UVIN} = 6 V	-	1	-	nA
OVIN input current	I _{OVIN}	V _{OVIN} = 6 V	-	1	-	nA
UVB Operating Voltage Range (Note 1)	V _{OPLUVB}	V _{OLUVB} ≤ 0.4 V, R _L = 100 kΩ	1.8	-	-	V
OVB Operating Voltage Range (Note 1)	V _{OPLOVB}	V _{OLOVB} ≤ 0.4 V, R _L = 100 kΩ	1.8	-	-	V
UVB "Low" Output Voltage	V _{OLUVB}	V _{UVIN} < V _{UVDET} , V _{DD} = 1.8 V, I _{SINK} = 2.0 mA	-	-	0.4	V
OVB "Low" Output Voltage	V _{OLOVB}	V _{OVIN} > V _{OVDDET} , V _{DD} = 1.8 V, I _{SINK} = 2.0 mA	-	-	0.4	V
UVB L→H Propagation Delay Time	t _{PLHUVB}	V _{UVB} = GND→0.9 x V _{DD} , V _{DD} = 12 V	-	17	40	μs
OVB L→H Propagation Delay Time	t _{PLHOVB}	V _{OVB} = GND→0.9 x V _{DD} , V _{DD} = 12 V	-	17	40	μs
UVB H→L Propagation Delay Time	t _{PHLUVB}	V _{UVB} = V _{DD} →0.1 x V _{DD} , V _{DD} = 12 V	-	12	35	μs
OVB H→L Propagation Delay Time	t _{PHLOVB}	V _{OVB} = V _{DD} →0.1 x V _{DD} , V _{DD} = 12 V	-	12	35	μs

R_L: Pull-up resistor connected between UVB, OVB and power supply.

(Note 1) When V_{DD} is less than V_{OPLUVB}, V_{OPLOVB}, outputs are unstable.

Typical Performance Curves

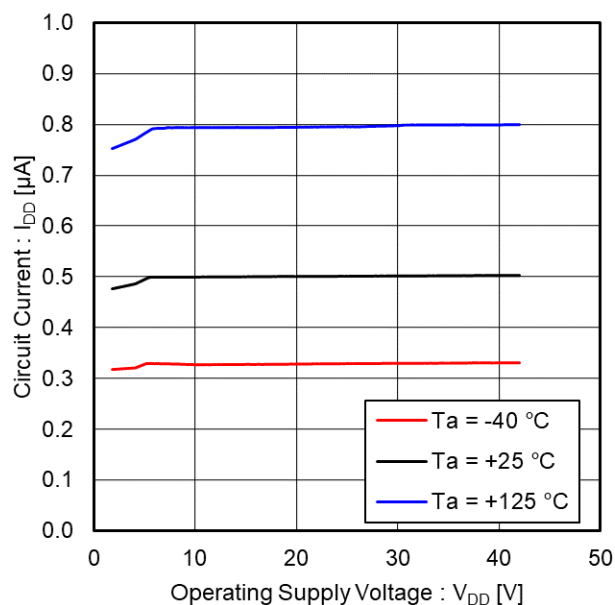


Figure 1. Circuit Current vs Operating Supply Voltage

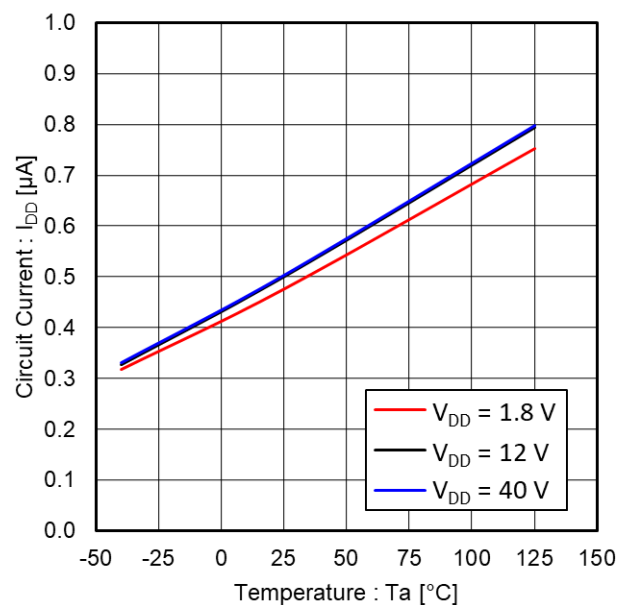
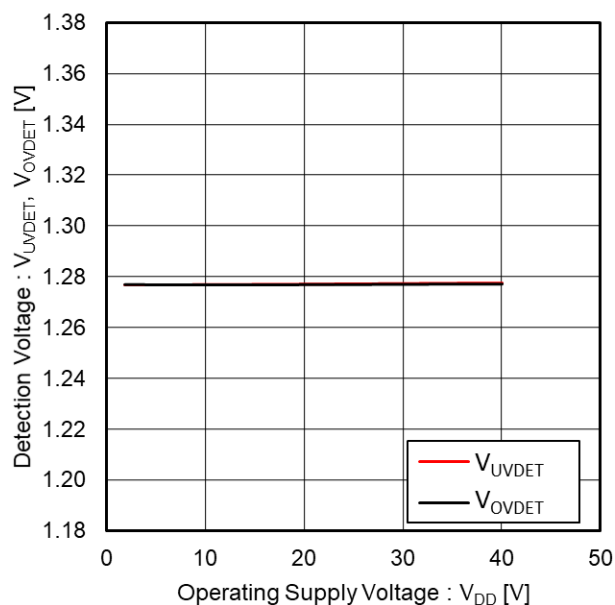
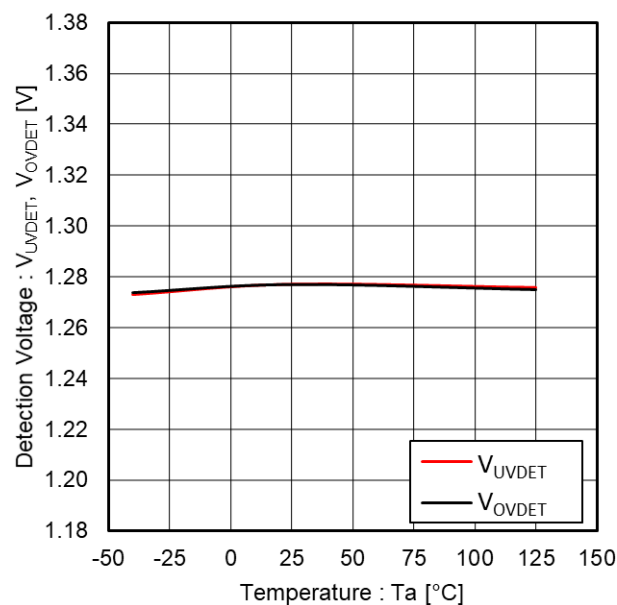


Figure 2. Circuit Current vs Temperature

Figure 3. Detection Voltage vs Operating Supply Voltage
(Ta = 25 °C)Figure 4. Detection Voltage vs Temperature
(V_DD = 12 V)

(Note) The above data are measurement value of typical sample; it is not guaranteed.

Typical Performance Curves – continued

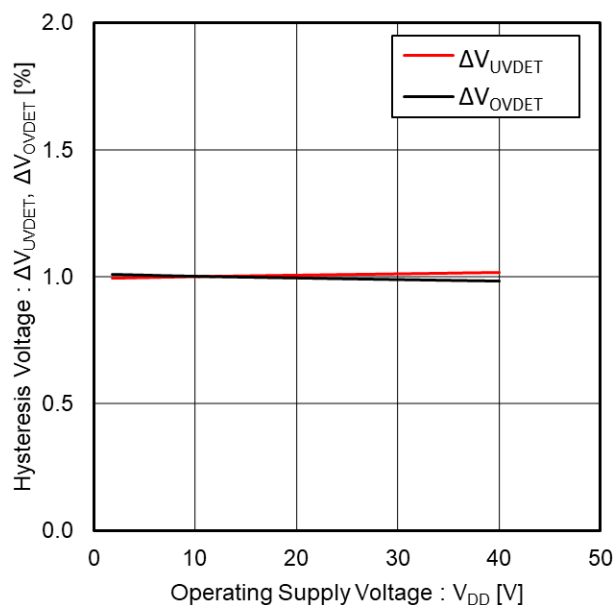
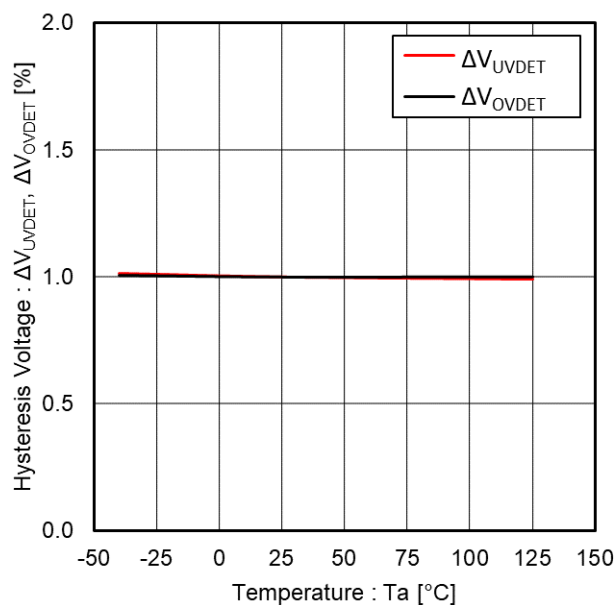
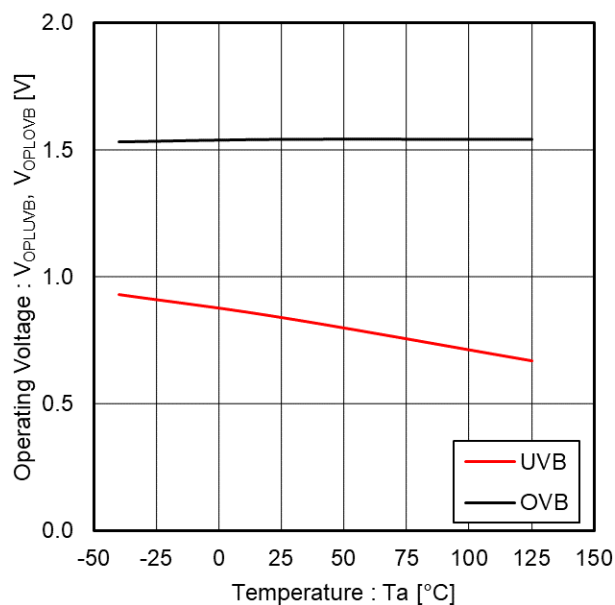
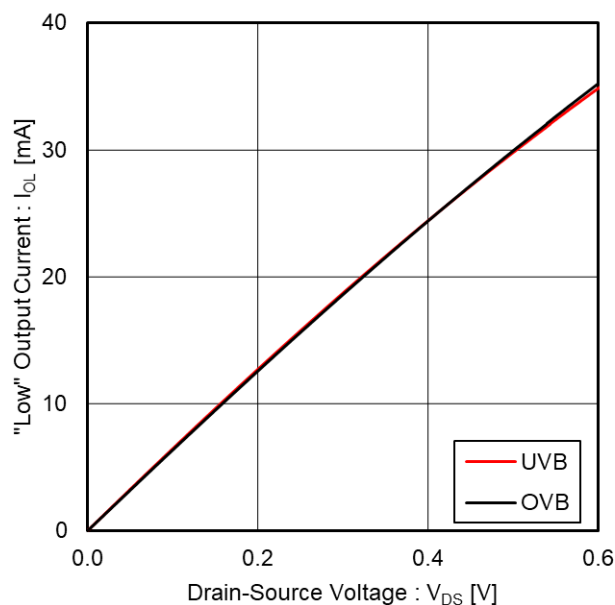
Figure 5. Hysteresis Voltage vs Operating Supply Voltage
($T_a = 25^\circ\text{C}$)Figure 6. Hysteresis Voltage vs Temperature
($V_{DD} = 12\text{ V}$)

Figure 7. Operating Voltage vs Temperature

Figure 8. "Low" Output Current vs Drain-Source Voltage
($V_{DD} = 1.8\text{ V}$, $T_a = 25^\circ\text{C}$)

(Note) The above data are measurement value of typical sample; it is not guaranteed.

Typical Performance Curves – continued

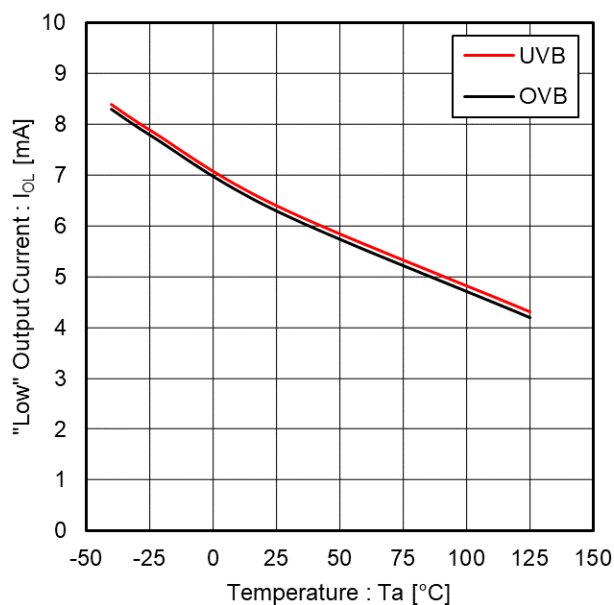


Figure 9. "Low" Output Current vs Temperature
($V_{DD} = 1.8\text{ V}$, $V_{DS} = 0.1\text{ V}$)

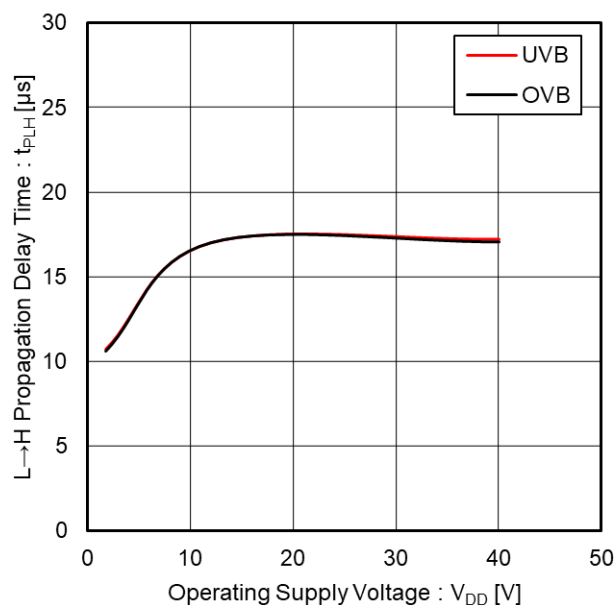


Figure 10. L→H Propagation Delay Time
vs Operating Supply Voltage
($T_a = 25\text{ °C}$)

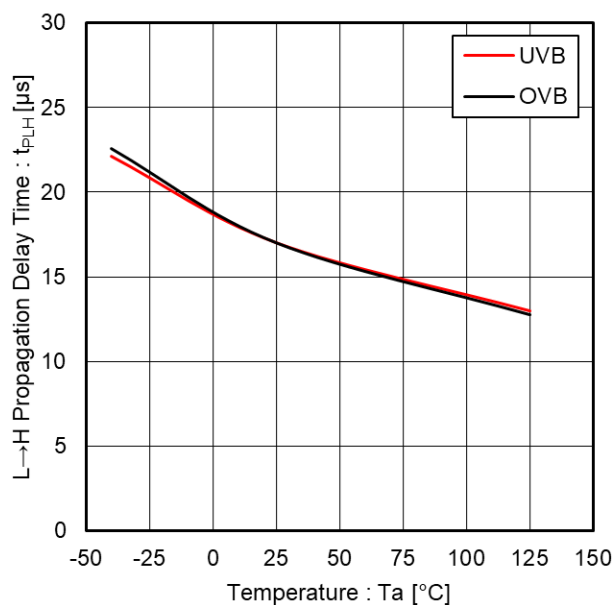


Figure 11. L→H Propagation Delay Time vs Temperature
($V_{DD} = 12\text{ V}$)

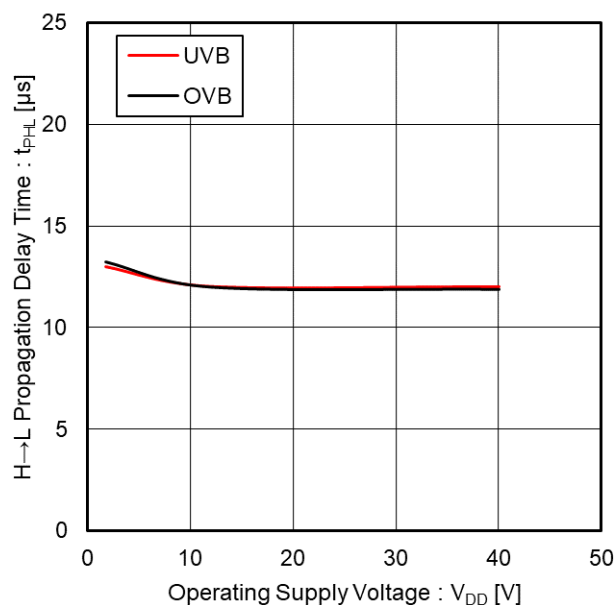


Figure 12. H→L Propagation Delay Time
vs Operating Supply Voltage
($T_a = 25\text{ °C}$)

(Note) The above data are measurement value of typical sample; it is not guaranteed.

Typical Performance Curves – continued

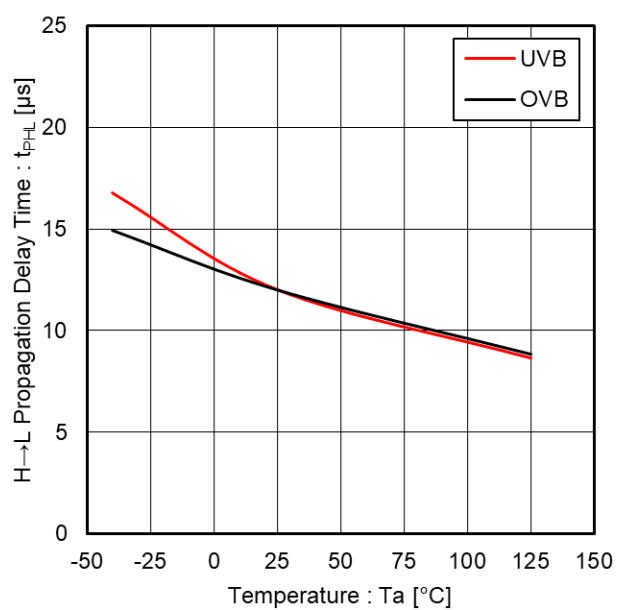


Figure 13. H→L Propagation Delay Time vs Temperature
($V_{DD} = 12$ V)

(Note) The above data are measurement value of typical sample; it is not guaranteed.

Timing Chart

The following shows the change of the output voltages when operating supply voltage (V_{DD}) and SENSE pin Voltage (V_{SENSE}) sweep.

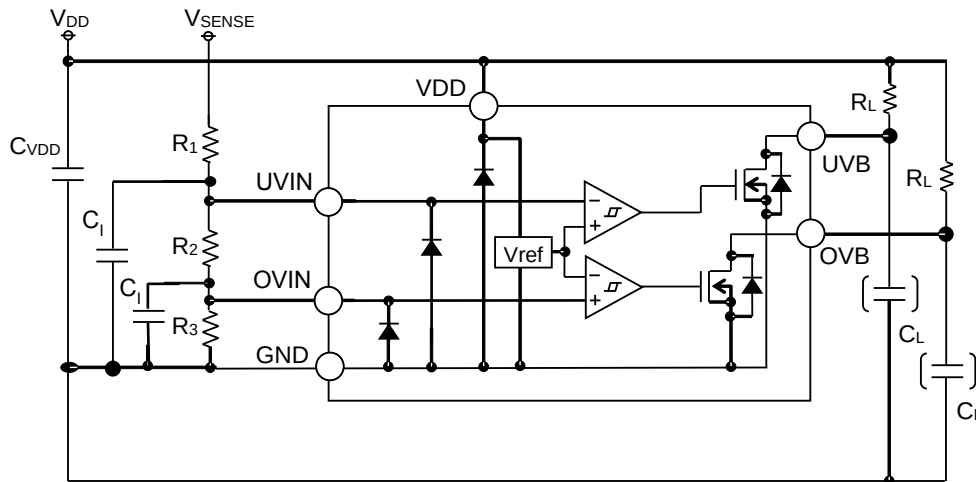


Figure 14. Set-up diagram

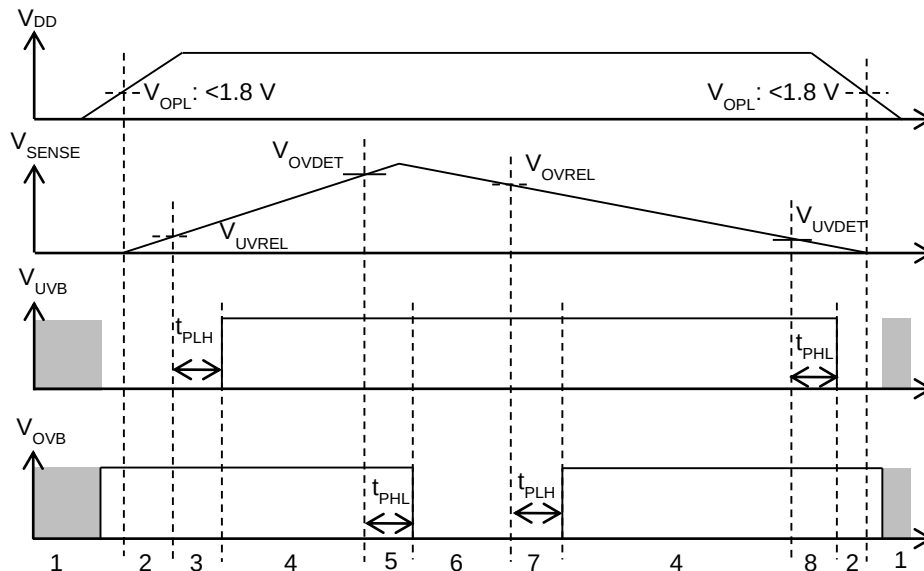


Figure 15. Timing Chart

Operating Conditions Explanation

1. The Output Voltage (V_{OVB} and V_{UVB}) becomes unstable until V_{DD} exceeds the Operating Voltage Range (V_{OPL}).
2. When V_{DD} exceeds the Operating Voltage Range (V_{OPL}) but V_{SENSE} is the Under Voltage Detection Voltage (V_{UVDET}) or less, V_{UVB} changes to "L" and V_{OVB} changes to "H". However, this change depends on the V_{UVB} and V_{OVB} rise time when the power supply starts up, so thorough confirmation is required.
3. When V_{SENSE} rises and exceeds the Under Voltage Release Voltage (V_{UVREL}), delay time (t_{PLH}) happens and V_{UVB} switches from "L" to "H".
4. Both Under Voltage and Over Voltage are undetected so V_{UVB} and V_{OVB} remains "H".
5. When V_{SENSE} rises further and exceeds the Over Voltage Detection Voltage (V_{OVDET}), delay time (t_{PHL}) happens and V_{OVB} changes from "H" to "L" and state becomes Over Voltage Detection.
6. V_{SENSE} is V_{OVDET} or more so V_{UVB} remains "H" and V_{OVB} remains "L".
7. When V_{SENSE} drops and falls below the Over Voltage Release Voltage (V_{OVREL}), delay time (t_{PLH}) happens and V_{OVB} switches from "L" to "H".
8. When V_{SENSE} decreases further and falls below the Under Voltage Detection Voltage (V_{UVDET}), delay time (t_{PHL}) happens and V_{UVB} changes from "H" to "L" and state becomes Under Voltage Detection.

(Note) The potential difference between the detection voltage and the release voltage is known as the Hysteresis Voltage width. The system is designed such that the output will not toggle with power supply fluctuations within this hysteresis width, preventing malfunctions due to noise.

Application Information

Operation Description

The detection and release voltage are used as threshold voltages. When the voltage applied to the UVIN and OVIN pins reaches the applicable threshold voltage, the V_{OV} and V_{UV} levels switch from either "H" to "L" or "L" to "H". Because the BD48HW0G-C uses an open drain output type, it is necessary to connect a pull-up resistor to V_{DD} or another power supply. (In this case, the output "H" voltage becomes V_{DD} or the voltage of another power supply).

Setting of External Resistors

Detection voltage of BD48HW0G-C can be control by external resistors. The resistance value of R_1 , R_2 and R_3 can be determined by the following formula. However, determine external resistance value so that the current flowing through external resistors is 10 μ A or more. In addition, when using, ensure that confirmation of the real function was carried out.

$$R_T = R_1 + R_2 + R_3$$

$$R_3 = \frac{R_T}{V_{OVDET}} \times V_{OV}$$

$$R_2 = \frac{R_T}{V_{UVDET}} \times V_{UV} - R_3$$

where:

R_T is the total value of external resistors.

V_{OV} is the over voltage detection voltage at the OVIN pin.

V_{UV} is the under voltage detection voltage at the UVIN pin.

Example No. 1:

$V_{UVDET} = 2.5 \text{ V}$, $V_{OVDET} = 3.5 \text{ V}$ ($R_T = 250 \text{ k}\Omega$)

$$R_3 = \frac{250 \times 10^3}{3.5} \times 1.277 = 91.2 \text{ k}\Omega$$

$$R_2 = \frac{250 \times 10^3}{2.5} \times 1.277 - 91.2 \times 10^3 = 36.5 \text{ k}\Omega$$

$$R_1 = 250 \times 10^3 - 91.2 \times 10^3 - 36.5 \times 10^3 = 122.3 \text{ k}\Omega$$

Bypass Capacitor for Noise Rejection

For the stable operation of the IC, put capacitor 0.1 μ F or more between the V_{DD} and GND pins and 100 pF or more between UVIN, OVIN and GND and connect it closer to the pin as possible. When using extremely big capacitors, the transient response speed becomes slow so check thoroughly.

External Parameters

The recommended value of pull-up resistance value is 10 $\text{k}\Omega$ to 1 $\text{M}\Omega$. Since the changes are brought by many factors (circuit configuration, board layout, etc.) when using, ensure that confirmation of the real function was carried out. In addition, this IC has high impedance design. So depending on the condition of use, this may be affected by unexpected leak route due to the uncleanness of PCB surface. For example, if a 10 $\text{M}\Omega$ leakage is assumed between the output and GND pins, it is recommended to set the value of pull-up resistor to 1/10 or less of the impedance of assumed leakage route.

Behavior at less than the Operating Voltage Range

When V_{DD} falls less than the operating voltage range, output will be undefined. When output is connected to pull-up voltage, output will be equivalent to pull-up voltage.

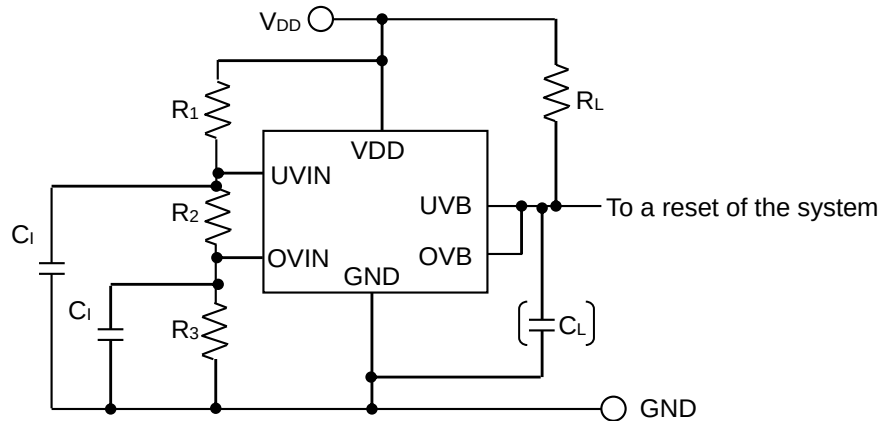
Precautions when Steep Power Supply Rise

In case of a steep power supply rise, the output may be unstable even if V_{DD} exceeds the operating voltage range. This is due to the undefined output when the supply is less than the operating voltage range of the IC. When this waveform affects the application, make the rise time slower by attaching capacitor to V_{DD} (C_{VDD}). Make the V_{DD} Rise Time is 1 ms or more.

Application Examples

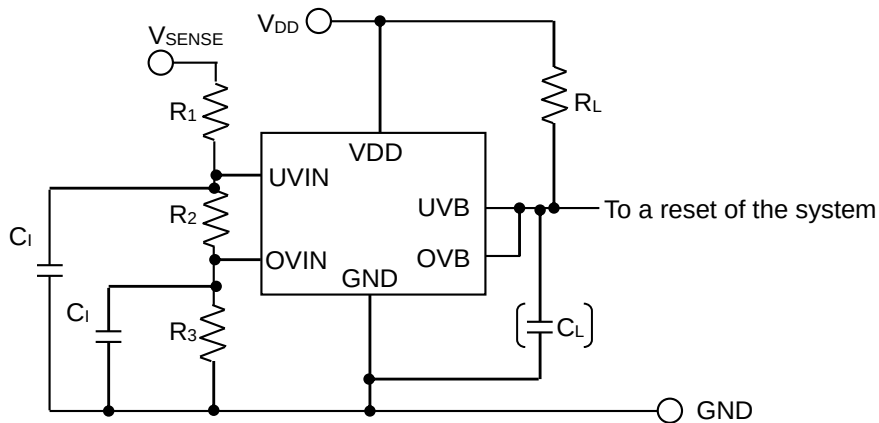
(1) Monitoring the power supply input pin of the IC

The following shows example of applications when monitoring the power supply input pin (V_{DD}) of the IC. The external resistors are connected between V_{DD} and GND.



(2) Monitoring the Voltage Other Than the power supply input pin of the IC

The following shows example of applications when monitoring the voltage other than V_{DD} . The external resistors are connected between V_{SENSE} and GND. The voltage exceeding maximum rating of V_{DD} can be detected by external resistors setting. Set UVIN and OVIN so that it does not exceed absolute maximum rating voltage.



When connecting a capacitor C_L for noise elimination and setting the output delay time to the output pin, the waveform is dull during rising and falling of the output so use after confirmation that there is no problem.

Application Examples - continued

(3) Examples of the Power Supply with Resistor Dividers

The following shows example of applications of a resistor divider circuit in applications which the resistor connected to the power supply voltage (V_{DD}) of an IC. In these applications, when the output logic changes its state, an Inrush current will flow suddenly into the circuit. This current flow may cause malfunction in the systems operation such as output oscillations, etc. The recommended value of R_A is 10 k Ω or less, and C_{VDD} is 0.1 μF or more. (Inrush current will flow suddenly from the power supply (V_{DD}) to GND when the output level switches to "H" or "L".)

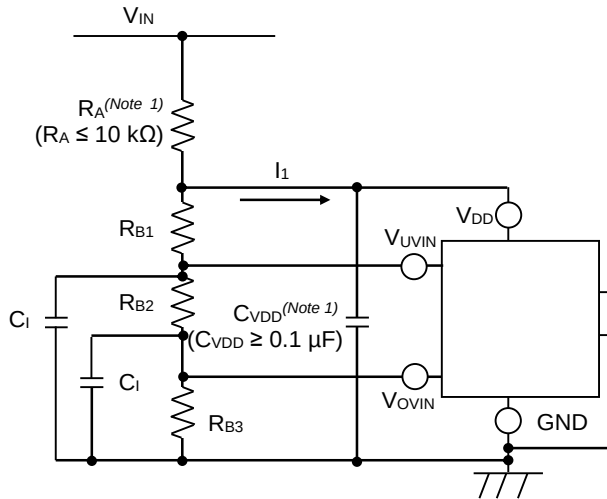
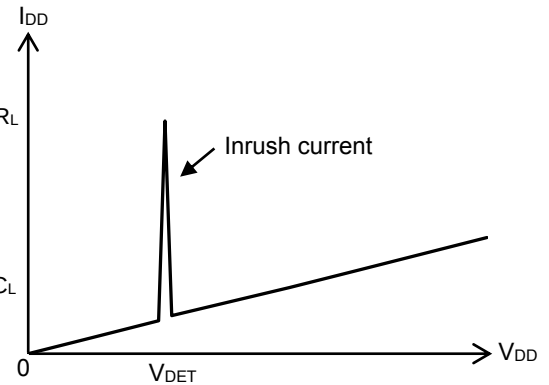
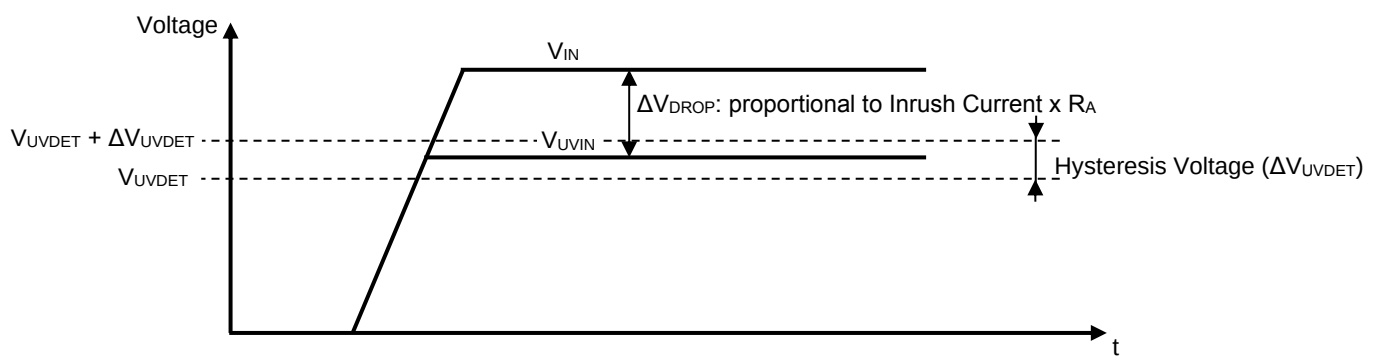


Figure 16. Resistor Divider Connection Application

Figure 17. Current Consumption vs V_{DD} Voltage

(Note 1) The circuit example mentioned above does not guarantee successful operation.
Perform thorough evaluation using the actual application and set countermeasures.

For example, during low voltage detection release, a voltage drop [$\text{Inrush current } (I_1) \times [\text{input resistor } (R_A)]$] is caused by the Inrush current when output changes from "L" to "H", and causes the input voltage to drop. When the input voltage drops and falls below the detection voltage, the output will switch from "H" to "L". At this time, the Inrush current stops flowing through output "L", and the voltage drop disappears. As a result, the output switches from "L" to "H", which again causes the Inrush current to flow and the voltage to drop. This operation repeats and leads to oscillation. In addition, note that the same phenomenon occurs during over voltage detection. Depending on the application set-up, there are times that V_{UVIN} voltage is always below the Release Voltage because of the effect of Inrush current as shown follows.

Figure 18. V_{UVIN} Drop Caused by Inrush Current

Application Examples - continued

(4) Considerations on Input and Output Capacitor

It is suggested to use capacitors between the input pin and GND, and the output pin and GND, which is positioned as near as possible to the pins. The capacitor between the input pin and GND is effective when the power supply impedance increases or when the wiring is long. A large capacitor between the output pin and GND improves stability and output load characteristics. Check the state of mounting. In addition, the ceramic capacitor deviates and has temperature characteristics and AC bias characteristics in general. Furthermore, depending on the usage, the capacitance value decreases over time. It is recommended that ceramic capacitor to use is decided after gathering detailed data information by consulting brand manufacturers.

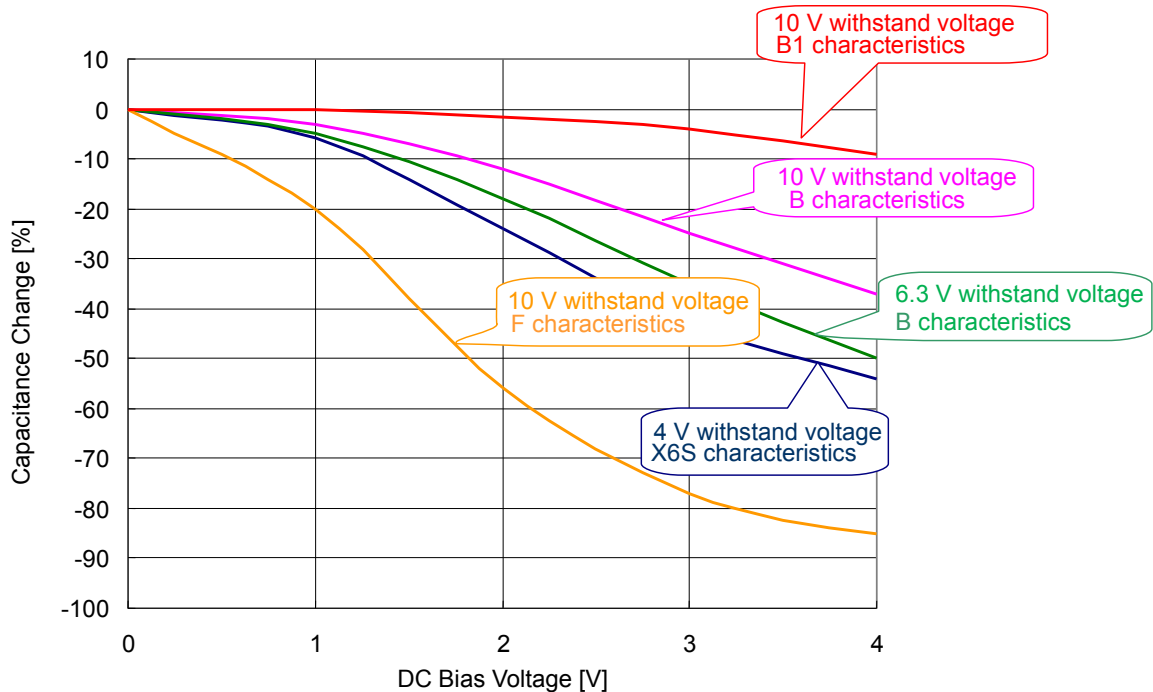
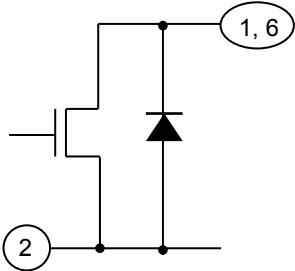
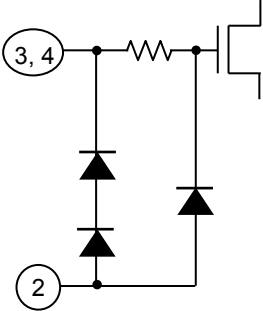


Figure 19. Ceramic Capacitance Change vs DC Bias voltage
(Characteristic example)

I/O Equivalence Circuits

Pin No.	Pin Name	Pin Description	Equivalence Circuit
1 6	UVB OVB	Under voltage detection output pin Over voltage detection output pin	
3 4	UVIN OVIN	Under voltage input Over voltage input	

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes – continued

10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When $GND > Pin\ A$ and $GND > Pin\ B$, the P-N junction operates as a parasitic diode.

When $GND > Pin\ B$, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

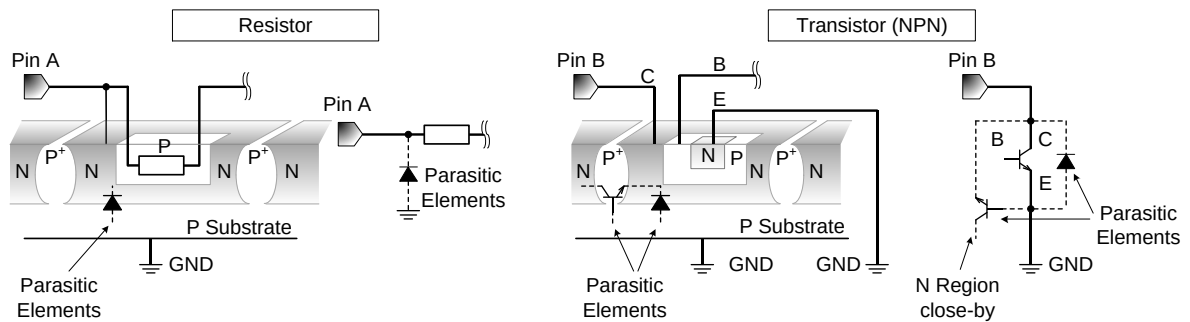


Figure 20. Example of Monolithic IC Structure

11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

12. Functional Safety

“ISO 26262 Process Compliant to Support ASIL-*”

A product that has been developed based on an ISO 26262 design process compliant to the ASIL level described in the datasheet.

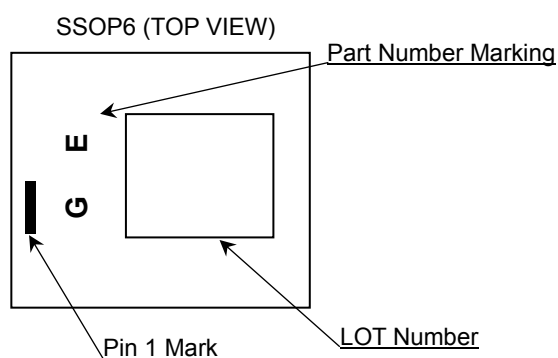
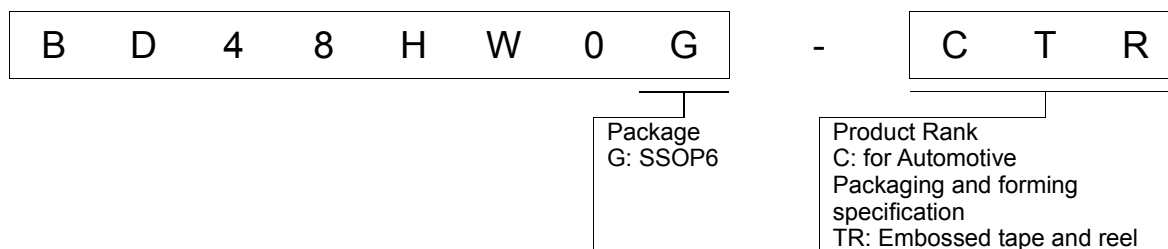
“Safety Mechanism is Implemented to Support Functional Safety (ASIL-*)”

A product that has implemented safety mechanism to meet ASIL level requirements described in the datasheet.

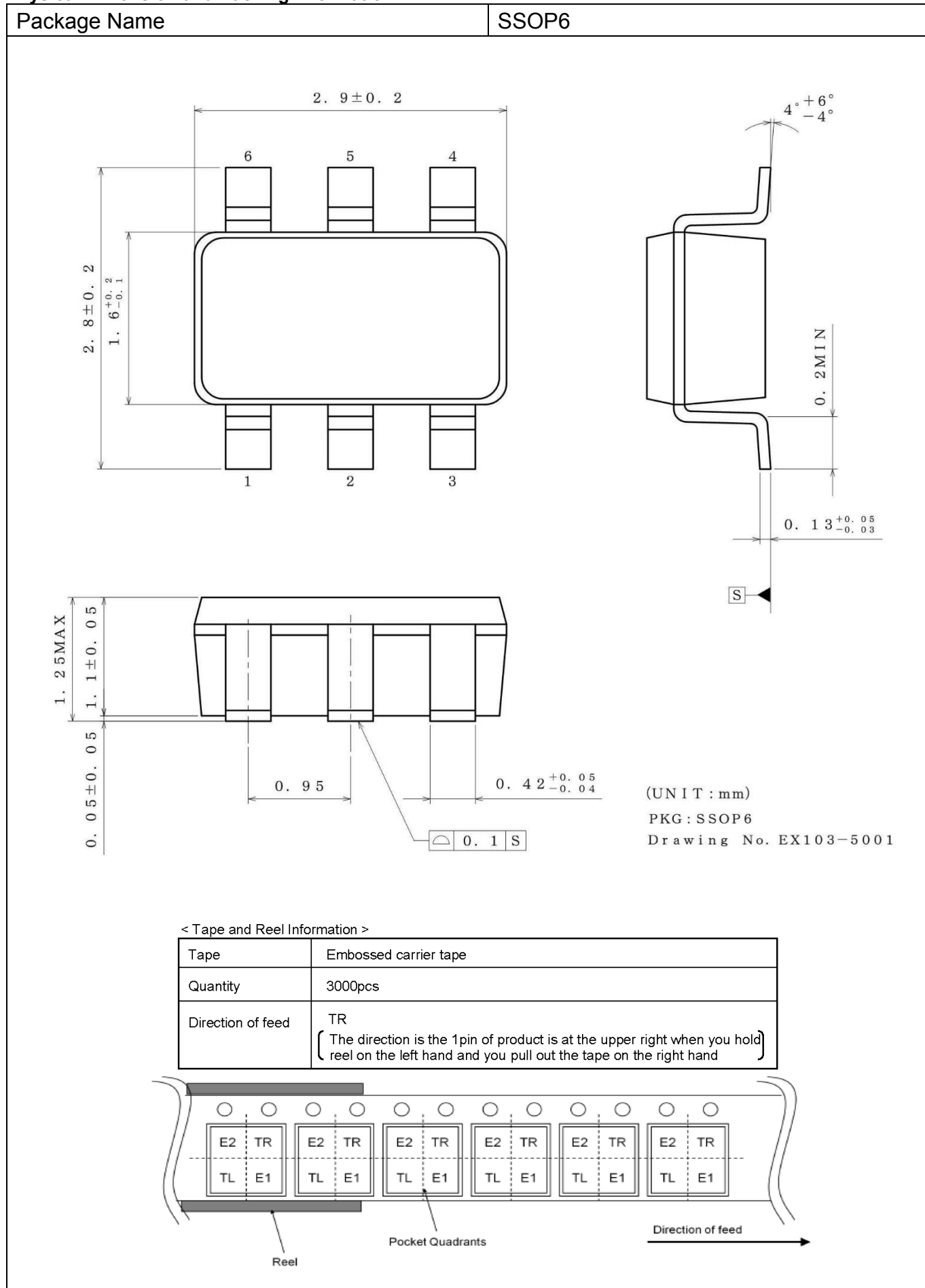
“Functional Safety Supportive Automotive Products”

A product that has been developed for automotive use and is capable of supporting safety analysis with regard to the functional safety.

Note: “ASIL-*” is stands for the ratings of “ASIL-A”, “-B”, “-C” or “-D” specified by each product's datasheet.



Physical Dimension and Packing Information



Revision History

Date	Revision	Changes
14.Feb.2022	001	New Release
13.Jul.2022	002	Clerical corrections

Notice

Precaution on using ROHM Products

1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment ^(Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASS III	CLASS III	CLASS II b	CLASS III
CLASS IV		CLASS III	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
4. The Products are not subject to radiation-proof design.
5. Please verify and confirm characteristics of the final or mounted products in using the Products.
6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
8. Confirm that operation temperature is within the specified range described in the product specification.
9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of ionizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

Precaution Regarding Intellectual Property Rights

1. All information and data including but not limited to application example contained in this document is for reference only. ROHM does not warrant that foregoing information or data will not infringe any intellectual property rights or any other rights of any third party regarding such information or data.
2. ROHM shall not have any obligations where the claims, actions or demands arising from the combination of the Products with other articles such as components, circuits, systems or external equipment (including software).
3. No license, expressly or implied, is granted hereby under any intellectual property rights or other rights of ROHM or any third parties with respect to the Products or the information contained in this document. Provided, however, that ROHM will not assert its intellectual property rights or other rights against you or your customers to the extent necessary to manufacture or sell products containing the Products, subject to the terms and conditions herein.

Other Precaution

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3. In no event shall you use in any way whatsoever the Products and the related technical information contained in the Products or this document for any military purposes, including but not limited to, the development of mass-destruction weapons.
4. The proper names of companies or products described in this document are trademarks or registered trademarks of ROHM, its affiliated companies or third parties.

General Precaution

1. Before you use our Products, you are requested to carefully read this document and fully understand its contents. ROHM shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any ROHM's Products against warning, caution or note contained in this document.
2. All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sales representative.
3. The information contained in this document is provided on an "as is" basis and ROHM does not warrant that all information contained in this document is accurate and/or error-free. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.